



UTT18N20H

Preliminary

POWER MOSFET

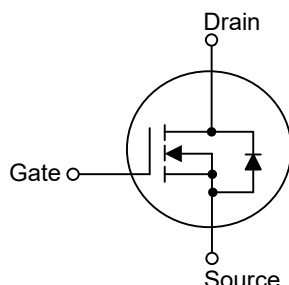
**18A, 200V N-CHANNEL
ENHANCEMENT MODE
TRENCH POWER MOSFET****DESCRIPTION**

The UTC **UTT18N20H** is a N-channel enhancement mode power MOSFET using UTC's advanced technology to provide customers with ideal for low voltage inverter applications.

The UTC **UTT18N20H** is suitable for high efficiency synchronous rectification in SMPS, UPS, hard switched and high frequency circuits.

FEATURES

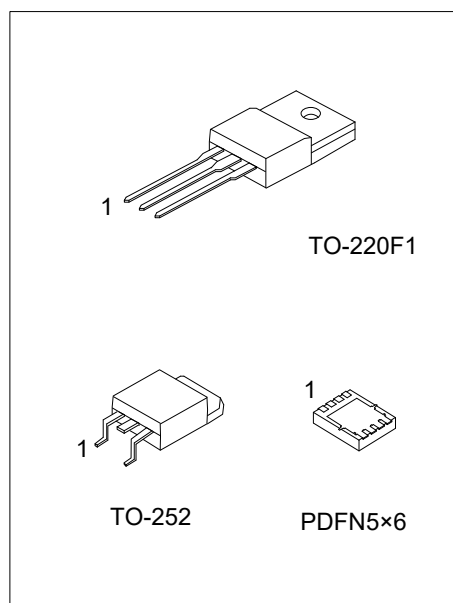
- * $R_{DS(ON)} \leq 125 \text{ m}\Omega$ @ $V_{GS}=10\text{V}$, $I_D=10\text{A}$
- * High Cell Density Trench Technology
- * High Power and Current Handling Capability

SYMBOL**ORDERING INFORMATION**

Ordering Number		Package	Pin Assignment								Packing
Lead Free	Halogen Free		1	2	3	4	5	6	7	8	
UTT18N20HL-TF1-T	UTT18N20HG-TF1-T	TO-220F1	G	D	S	-	-	-	-	-	Tube
UTT18N20HL-TN3-R	UTT18N20HG-TN3-R	TO-252	G	D	S	-	-	-	-	-	Tape Reel
UTT18N20HL-P5060-R	UTT18N20HG-P5060-R	PDFN5x6	S	S	S	G	D	D	D	D	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

UTT18N20HG-TF1-T		(1)Packing Type	(1) T: Tube, R: Tape Reel
		(2)Package Type	(2) TF1: TO-220F1, TN3: TO-252, P5060: PDFN5x6
		(3)Green Package	(3) G: Halogen Free and Lead Free, L: Lead Free



■ MARKING

TO-220F1 / TO-252	PDFN5×6
UTC UTT 18N20H □□□□□ 1 Lot Code → Date Code L: Lead Free G: Halogen Free	UTC UTT 18N20H • □□□□□ Lot Code → Date Code

■ **ABSOLUTE MAXIMUM RATINGS** ($T_C=25^{\circ}\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	200	V
Gate-Source Voltage		V_{GSS}	± 20	V
Continuous Drain Current	Continuous	I_{D}	18	A
Pulsed Drain Current	Pulsed (Note 2)	I_{DM}	54	A
Peak Diode Recovery dv/dt (Note 4)		dv/dt	2.8	V/nS
Power Dissipation	TO-220F1	P_{D}	40	W
	TO-252		54	W
	PDFN5×6		14	W
Junction Temperature		T_{J}	+150	$^{\circ}\text{C}$
Storage Temperature Range		T_{STG}	-55 ~ +150	$^{\circ}\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating: Pulse width limited by maximum junction temperature.

3. $I_{\text{SD}} \leq 18\text{A}$, $di/dt \leq 200\text{A}/\mu\text{s}$, $V_{\text{DD}} \leq V_{(\text{BR})\text{DSS}}$, $T_{\text{J}} = 25^{\circ}\text{C}$.

■ **THERMAL DATA**

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220F1	θ_{JA}	62.5	$^{\circ}\text{C}/\text{W}$
	TO-252		110	$^{\circ}\text{C}/\text{W}$
	PDFN5×6		65 (Note)	$^{\circ}\text{C}/\text{W}$
Junction to Case	TO-220F1	θ_{JC}	3.125	$^{\circ}\text{C}/\text{W}$
	TO-252		2.31 (Note)	$^{\circ}\text{C}/\text{W}$
	PDFN5×6		8.93 (Note)	$^{\circ}\text{C}/\text{W}$

Note: Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

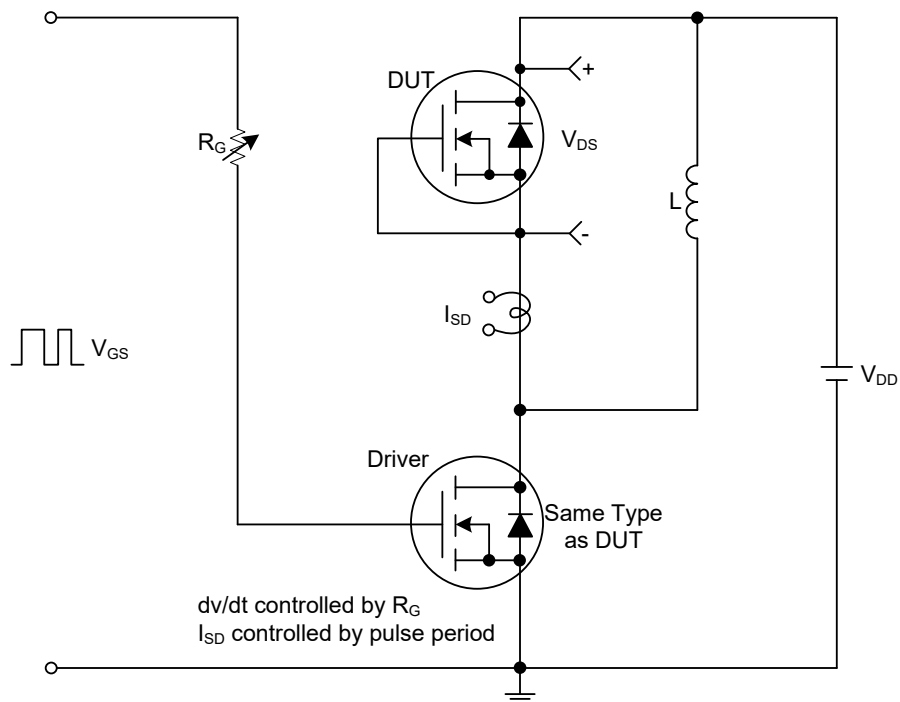
■ ELECTRICAL CHARACTERISTICS (T_J=25°C, unless otherwise specified)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS							
Drain-Source Breakdown Voltage		BV _{DSS}	I _D =250uA, V _{GS} =0V	200			V
Drain-Source Leakage Current		I _{DSS}	V _{DS} =200V, V _{GS} =0V			1	μA
Gate-Source Leakage Current	Forward	I _{GSS}	V _{GS} =+20V, V _{DS} =0V			+100	nA
	Reverse		V _{GS} =-20V, V _{DS} =0V			-100	nA
ON CHARACTERISTICS							
Gate Threshold Voltage		V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static Drain-Source On-State Resistance		R _{DS(ON)}	V _{GS} =10V, I _D =10A			125	mΩ
DYNAMIC PARAMETERS							
Input Capacitance		C _{ISS}	V _{GS} =0V, V _{DS} =25V, f=1.0MHz		2650		pF
Output Capacitance		C _{OSS}			140		pF
Reverse Transfer Capacitance		C _{RSS}			82		pF
SWITCHING PARAMETERS							
Total Gate Charge (Note 1)		Q _G	V _{DS} =160V, V _{GS} =10V, I _D =18A, (Note 1, 2)		76		nC
Gate to Source Charge		Q _{GS}			19		nC
Gate to Drain Charge		Q _{GD}			22		nC
Turn-on Delay Time (Note 1)		t _{D(ON)}	V _{DS} =100V, V _{GS} =10V, I _D =18A, R _G =25Ω (Note 1, 2)		14.4		ns
Rise Time		t _R			22		ns
Turn-off Delay Time		t _{D(OFF)}			46		ns
Fall-Time		t _F			24		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS							
Maximum Body-Diode Continuous Current		I _S				18	A
Maximum Body-Diode Pulsed Current		I _{SM}				54	A
Drain-Source Diode Forward Voltage (Note 1)		V _{SD}	I _S =20A, V _{GS} =0V			1.2	V
Reverse recovery time (Note 1)		t _{rr}	I _S =18A, V _{GS} =0V,		120		ns
Reverse recovery charge		Q _{rr}	dI _F /dt = 100A/μs		460		nC

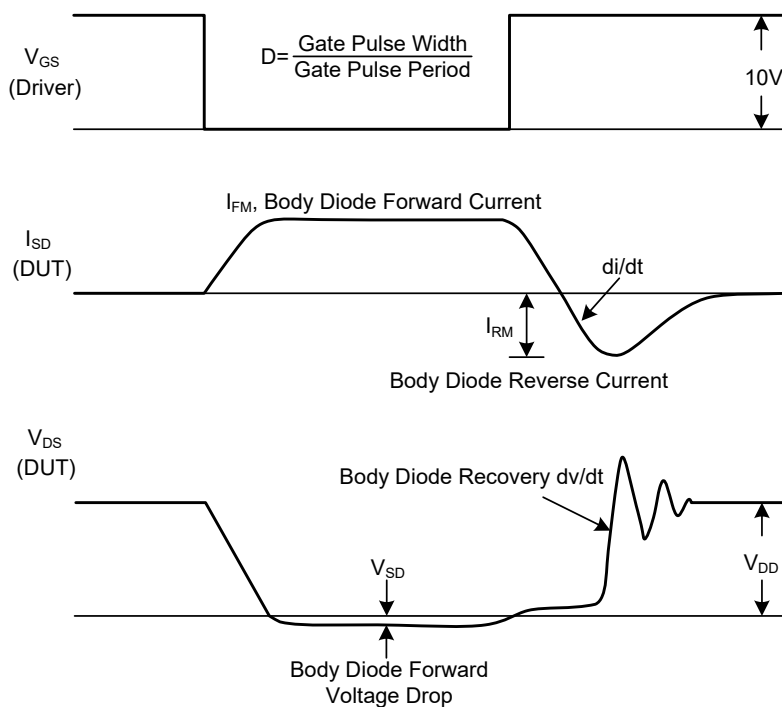
Notes: 1. Pulse Test: Pulse width ≤ 300μs, Duty cycle ≤ 2%.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS



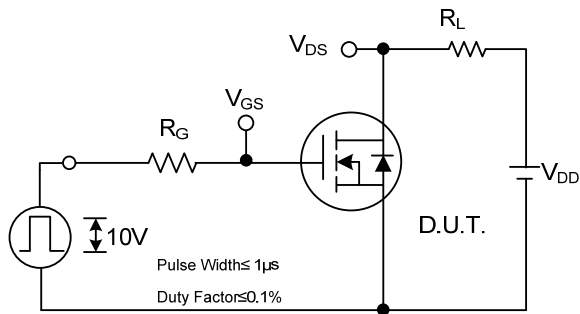
Peak Diode Recovery dv/dt Test Circuit



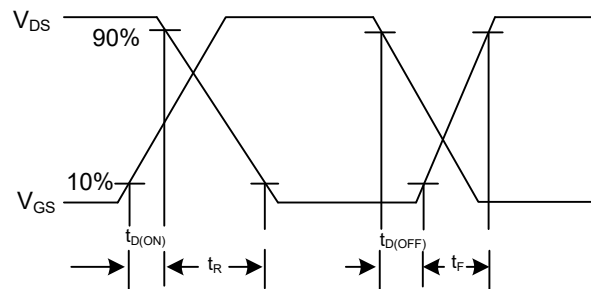
Peak Diode Recovery dv/dt Test Circuit and Waveforms

Peak Diode Recovery dv/dt Waveforms

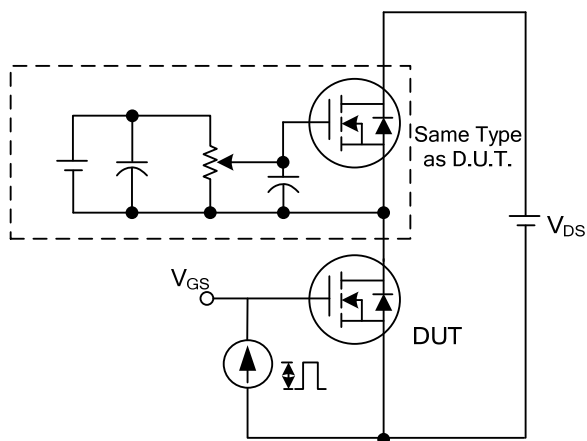
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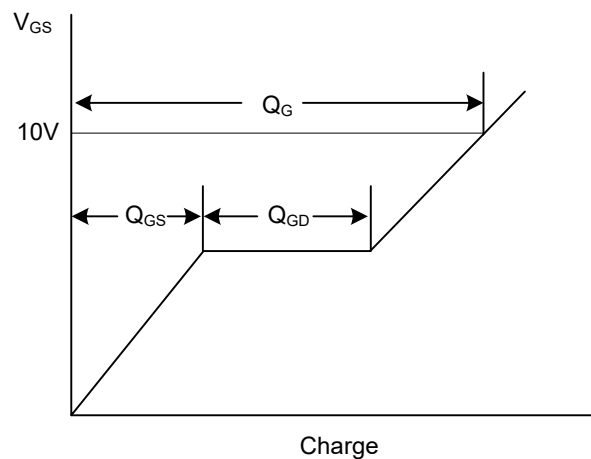
Switching Test Circuit



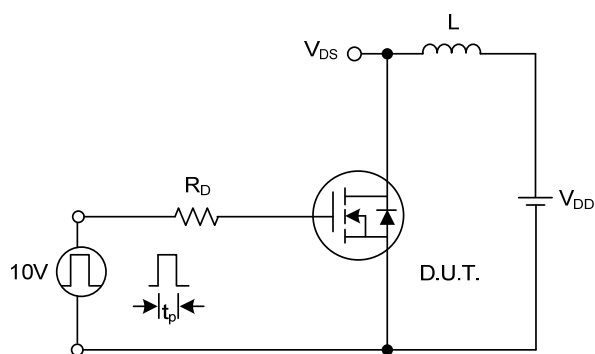
Switching Waveforms



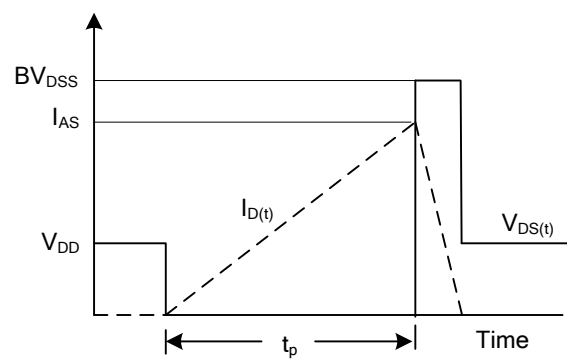
Gate Charge Test Circuit



Gate Charge Waveform



Unclamped Inductive Switching Test Circuit



Unclamped Inductive Switching Waveforms

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